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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Patent Application of

Ichiro FUJIWARA

Serial No.: 09/431,076

Filed: November 1, 1999

For: NONVOLATILE SEMICONDUCTOR)
 MEMORY DEVICE AND PROCESS)
 OF PRDUCTION AND WRITE METHOD)
 THEREOF)



) Art Unit: 2812

) Examiner: To Be Assigned

TC 2800 MAIL ROOM
MAY - 4 2000

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PRELIMINARY AMENDMENT

Assistant Commissioner of Patents
Washington, DC 20231

Sir:

Prior to the initial examination, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 1, line 12, change "etc." to --and so forth--.

Page 6, line 25, change "comprises" to --comprise--.

Page 7, line 5, change "a plurality of gate electrode" to --A plurality of gate electrodes--.

Page 7, line 10, change "polarity same to" to --polarity that is the same as--.

Page 7, line 18, change "contracted" to --contacted--.

Page 8, line 16, after "bias" delete "a".

Page 8, line 21, after "bias" delete "a".

Page 8, line 25, delete "a".

Page 9, line 2, after "equal" insert --to--.